

International Rectifier

PD - 9.767A

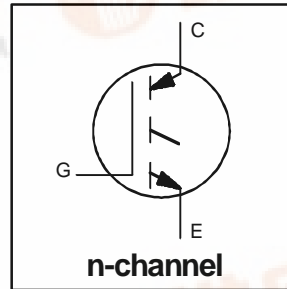
IRGPF50F

INSULATED GATE BIPOLAR TRANSISTOR

Fast Speed IGBT

Features

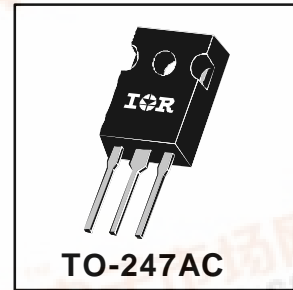
- Switching-loss rating includes all "tail" losses
- Optimized for medium operating frequency (1 to 10kHz) See Fig. 1 for Current vs. Frequency curve



$V_{CES} = 900V$
$V_{CE(sat)} \leq 2.7V$
@ $V_{GE} = 15V, I_C = 28A$

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	900	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	51	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	28	
I_{CM}	Pulsed Collector Current $\text{\textcircled{1}}$	100	
I_{LM}	Clamped Inductive Load Current $\text{\textcircled{2}}$	100	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy $\text{\textcircled{3}}$	20	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	78	
T_J	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
T_{STG}			
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	-----	-----	0.64	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	-----	0.24	-----	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	-----	-----	40	
Wt	Weight	-----	6 (0.21)	-----	g (oz)



Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	900	----	----	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ^④	20	----	----	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	----	0.74	----	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	----	2.1	2.7	V	$I_C = 28A$ $I_C = 51A$ $I_C = 28A, T_J = 150^\circ\text{C}$ $V_{GE} = 15V$ See Fig. 2, 5
		----	2.7	----		
		----	2.4	----		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	----	5.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	----	-9.7	----	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ^⑤	12	18	----	S	$V_{CE} = 100V, I_C = 28A$
I_{CES}	Zero Gate Voltage Collector Current	----	----	250	μA	$V_{GE} = 0V, V_{CE} = 900V$
		----	----	2000		$V_{GE} = 0V, V_{CE} = 900V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	----	----	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions		
Q_g	Total Gate Charge (turn-on)	----	81	120	nC	$I_C = 28A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig. 8		
Q_{ge}	Gate - Emitter Charge (turn-on)	----	16	24				
Q_{gc}	Gate - Collector Charge (turn-on)	----	29	44				
$t_{d(on)}$	Turn-On Delay Time	----	32	----	ns	$T_J = 25^\circ\text{C}$ $I_C = 28A, V_{CC} = 720V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail"		
t_r	Rise Time	----	22	----				
$t_{d(off)}$	Turn-Off Delay Time	----	200	280				
t_f	Fall Time	----	130	180				
E_{on}	Turn-On Switching Loss	----	1.1	----			mJ	See Fig. 9, 10, 11, 14
E_{off}	Turn-Off Switching Loss	----	1.8	----				
E_{ts}	Total Switching Loss	----	2.9	4.1				
$t_{d(on)}$	Turn-On Delay Time	----	32	----	ns	$T_J = 150^\circ\text{C}$, $I_C = 28A, V_{CC} = 720V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail"		
t_r	Rise Time	----	20	----				
$t_{d(off)}$	Turn-Off Delay Time	----	480	----				
t_f	Fall Time	----	450	----				
E_{ts}	Total Switching Loss	----	5.7	----			mJ	See Fig. 10, 14
L_E	Internal Emitter Inductance	----	13	----	nH	Measured 5mm from package		
C_{ies}	Input Capacitance	----	2300	----	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7		
C_{oes}	Output Capacitance	----	180	----				
C_{res}	Reverse Transfer Capacitance	----	27	----				

Notes:

- ① Repetitive rating; $V_{GE}=20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC}=80\%(V_{CES}), V_{GE}=20V, L=10\mu H, R_G=5.0\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

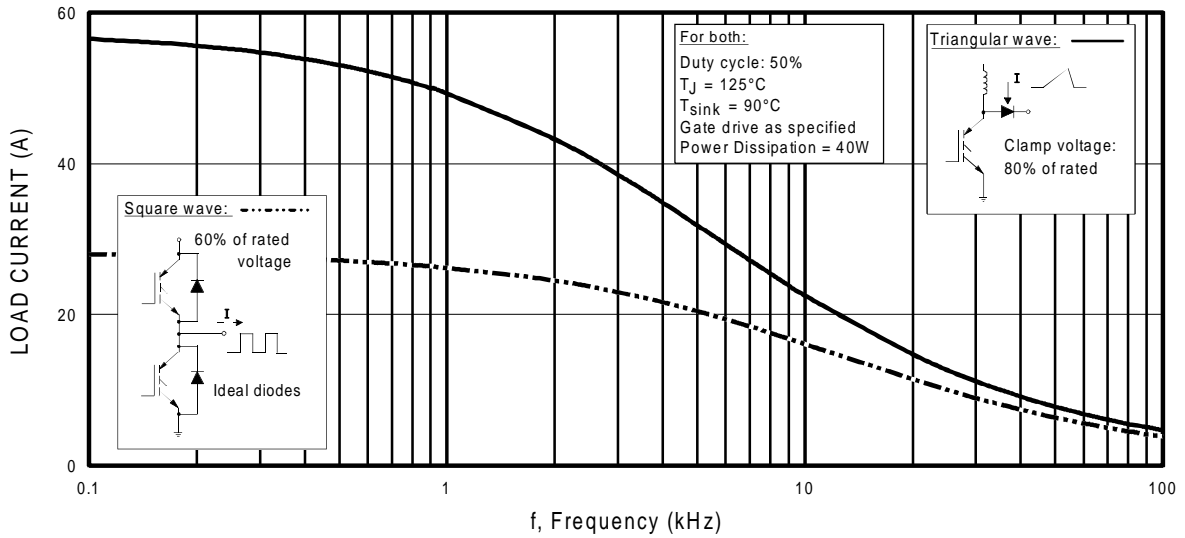


Fig. 1 - Typical Load Current vs. Frequency
 (For square wave, $I = I_{RMS}$ of fundamental; for triangular wave, $I = I_{PK}$)

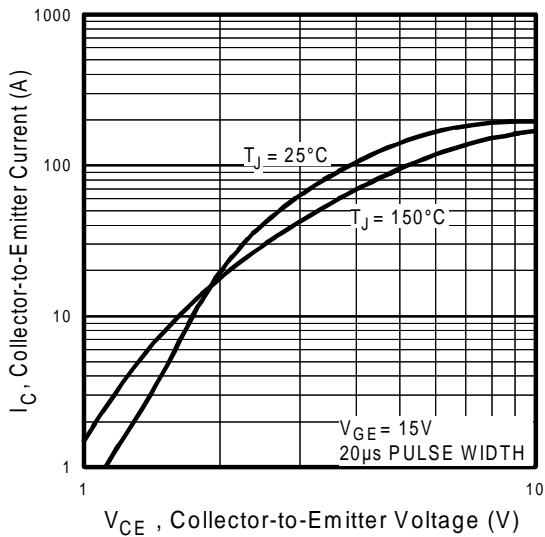


Fig. 2 - Typical Output Characteristics

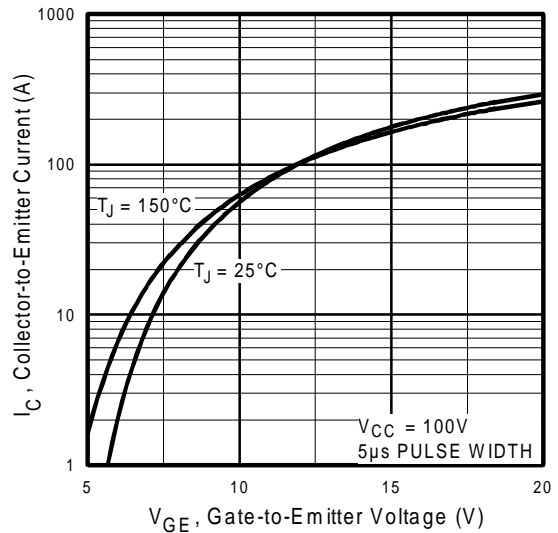


Fig. 3 - Typical Transfer Characteristics

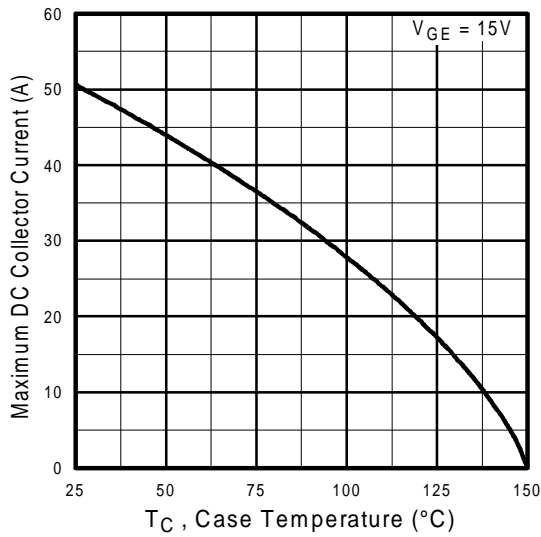


Fig. 4 - Maximum Collector Current vs. Case Temperature

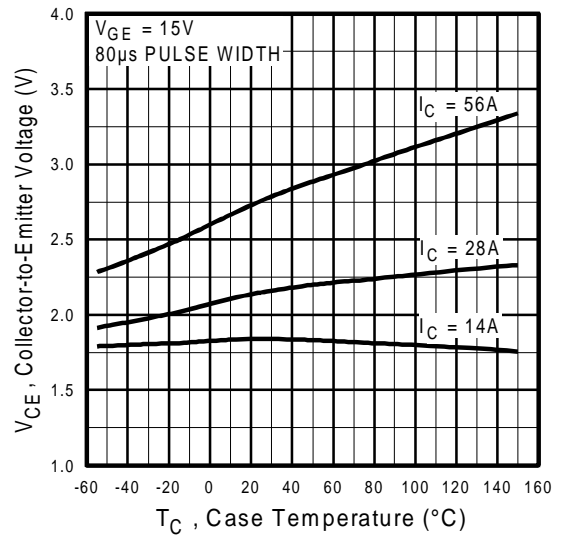


Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

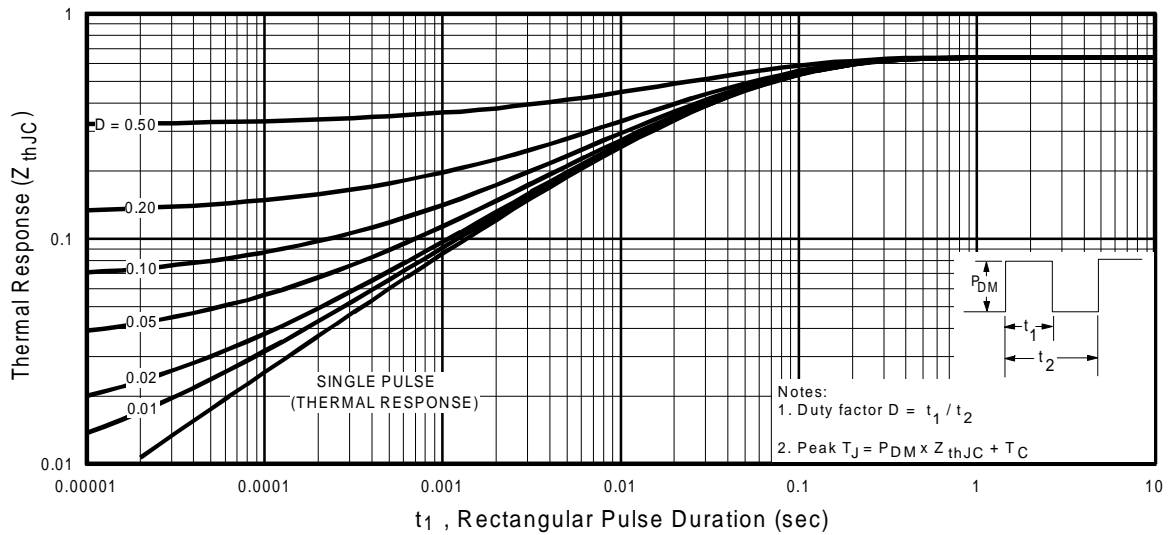


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

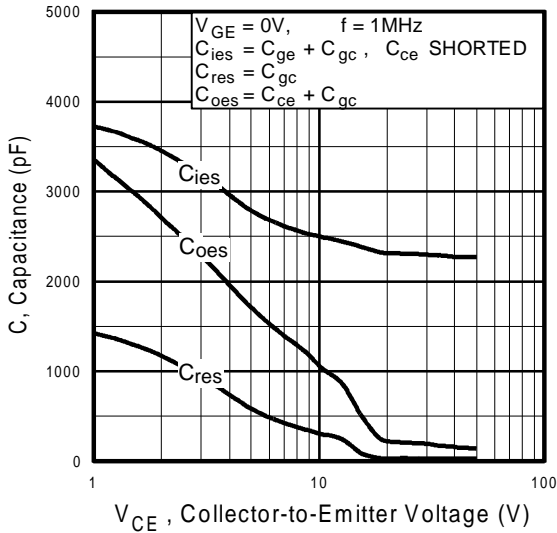


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

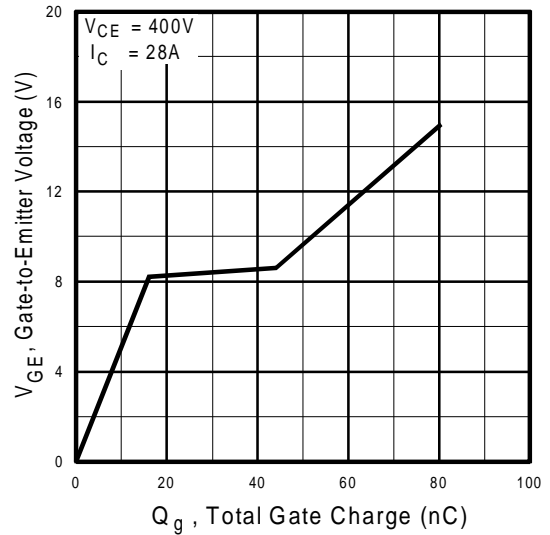


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

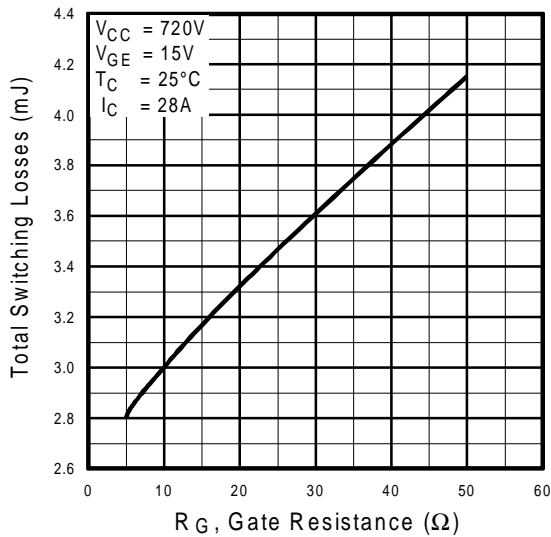


Fig. 9 - Typical Switching Losses vs. Gate Resistance

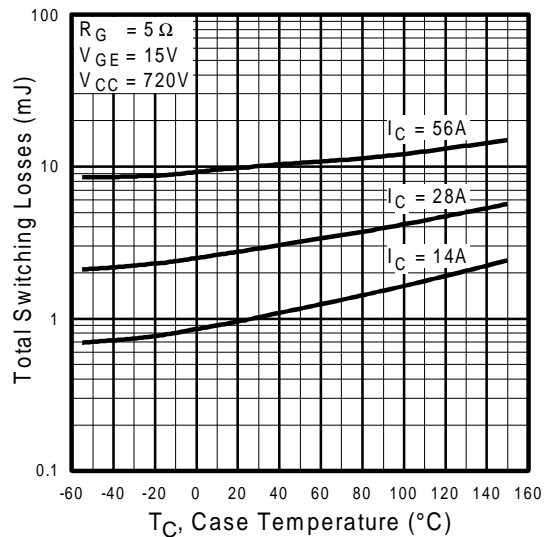


Fig. 10 - Typical Switching Losses vs. Case Temperature

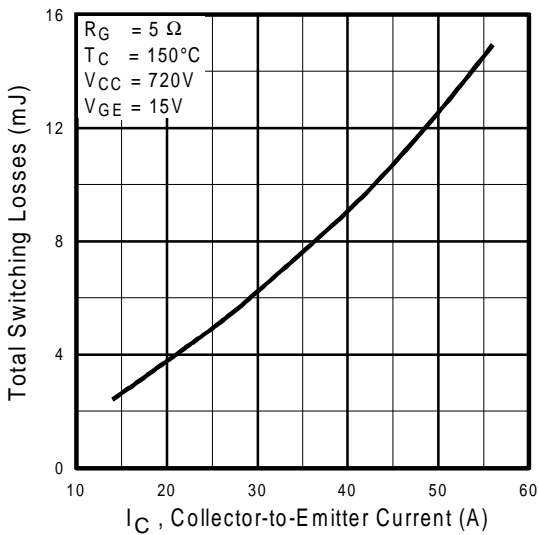


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

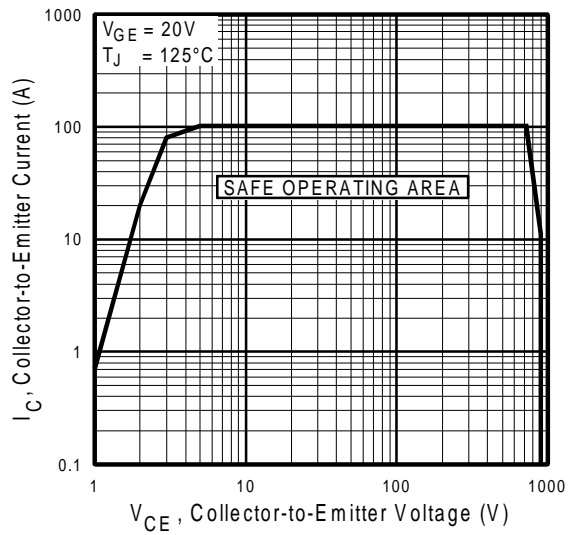


Fig. 12 - Turn-Off SOA

Refer to Section D for the following:

Appendix F: Section D - page D-8

- Fig. 13a - Clamped Inductive Load Test Circuit
- Fig. 13b - Pulsed Collector Current Test Circuit
- Fig. 14a - Switching Loss Test Circuit
- Fig. 14b - Switching Loss Waveform

Package Outline 3 - JEDEC Outline TO-247AC (TO-3P) Section D - page D-13